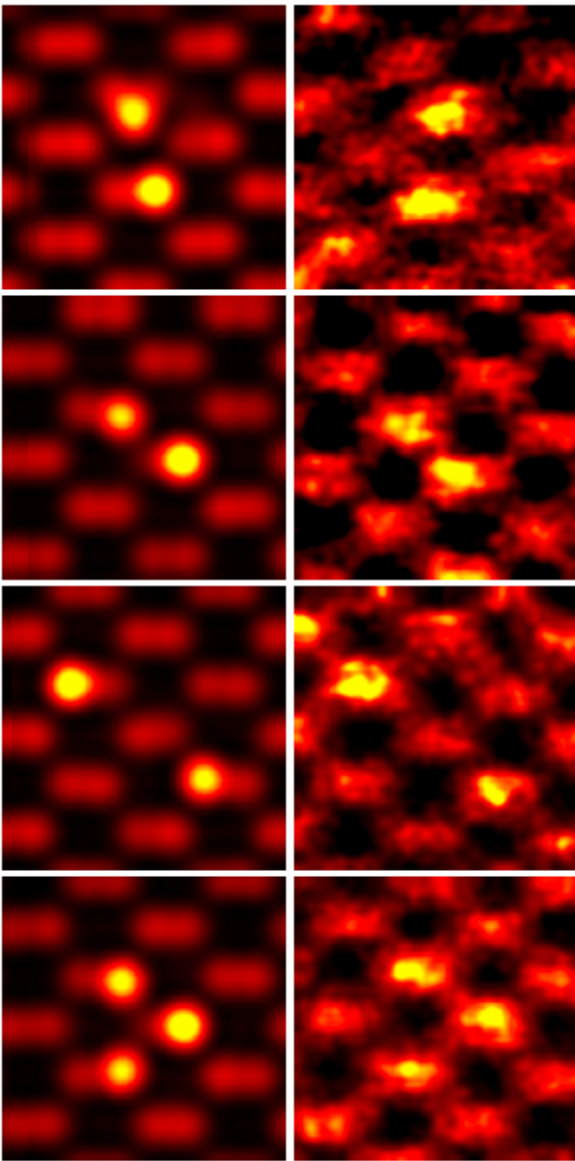


Future Nanocharacterization with Electrons: sub-Ångstrom, sub-eV, and Single Atom

Paul M. Voyles

Dept. of Materials
Science and Engineering

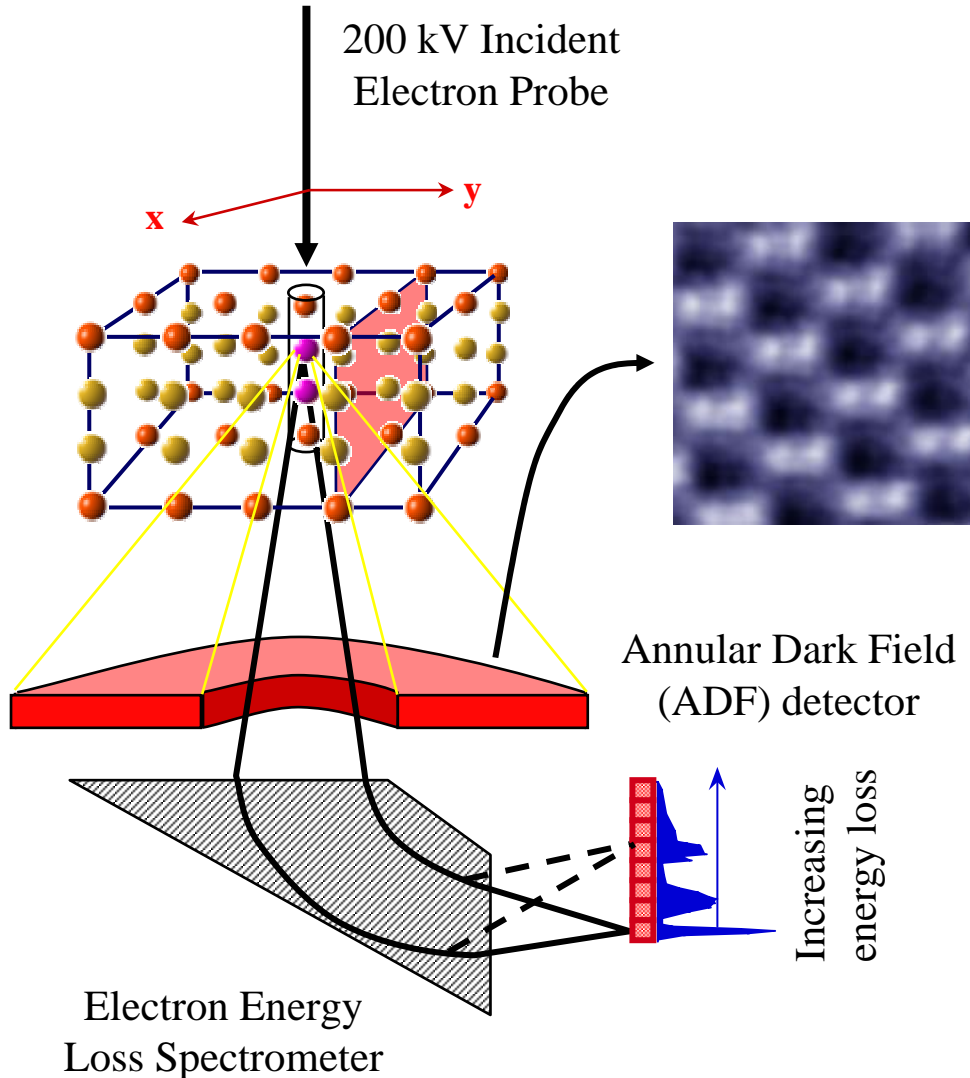
THE UNIVERSITY
of
WISCONSIN
MADISON



1 nm

- New technology and new capabilities: aberration correctors and monochromators
- New applications:
 - imaging and chemical analysis with single-atom sensitivity
 - imaging & spectroscopy of point defects
 - local valence-band spectroscopy
 - 3D, atomic scale imaging by tomography and optical sectioning
 - coherent scattering at nanometer resolution

Scanning Transmission Electron Microscope



- atomic diameter probe raster scanned
- high-angle detector (no Bragg beams)
- low-angle, BF, and spectrometer also available
- views structure in projection along the beam direction

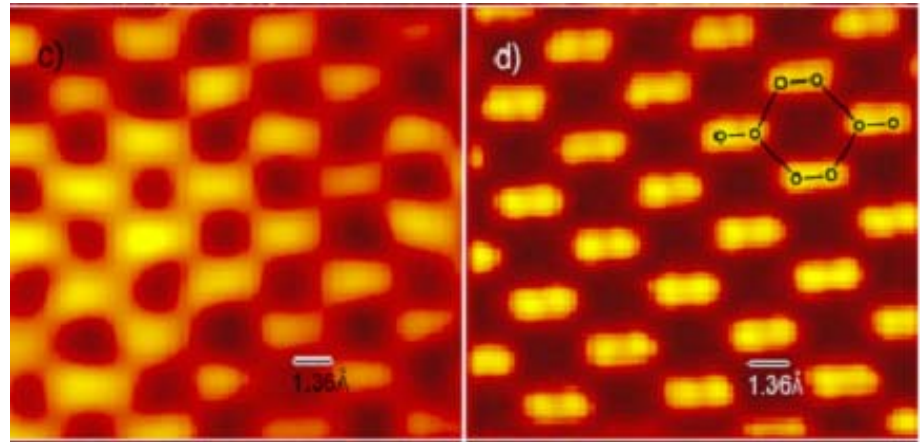
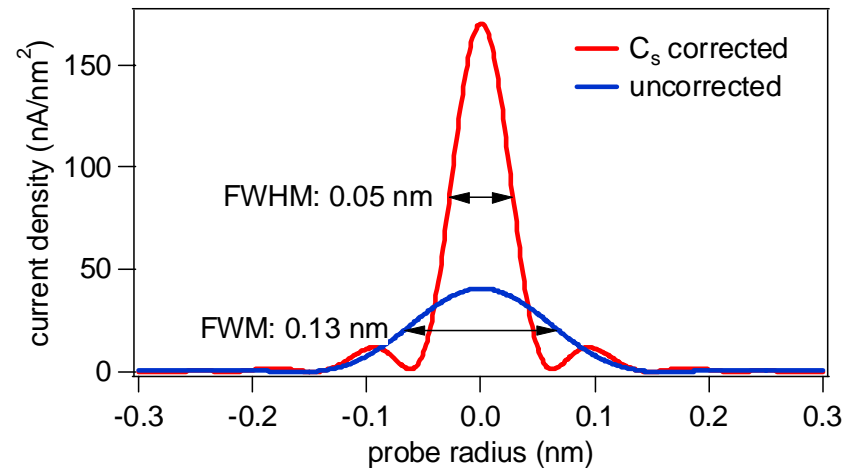
Aberrations & Correcting Them

Current electron lenses have large 3rd order spherical aberration:

optical micrograph



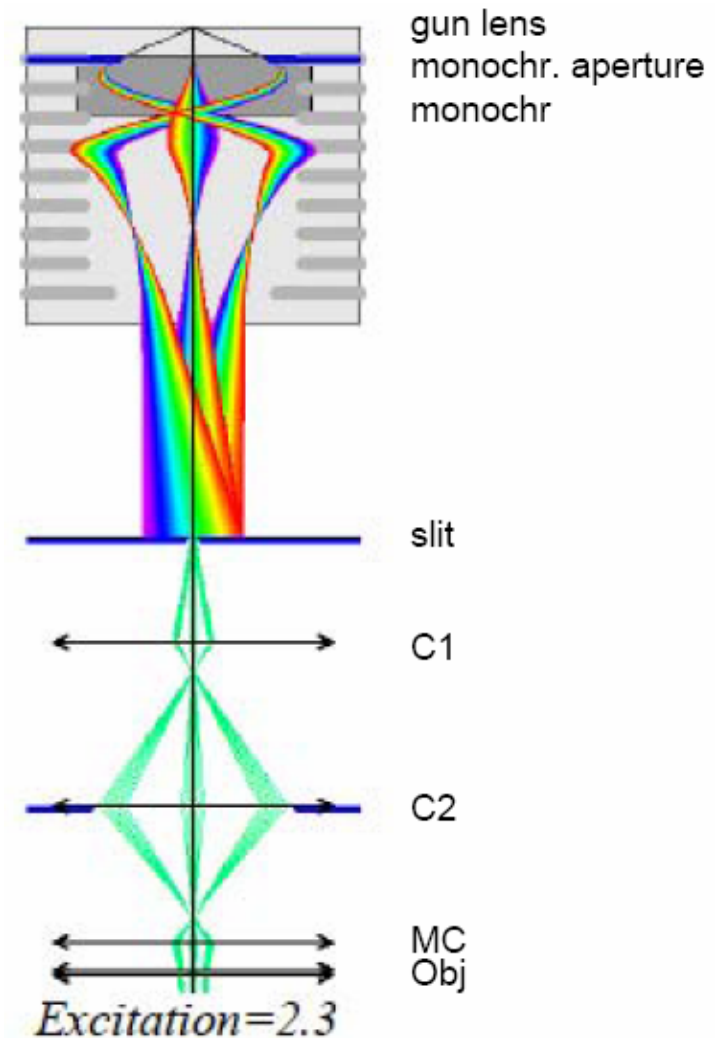
same micrograph
with EM-like C_s



P.E. Batson, N. Dellby, O.L. Krivanek,
Nature **418**, 617 (2002).

Monochromators

- TEM spectroscopic resolution limited by ΔE of the beam.
- Beam ΔE controlled by e-e scattering near the emitter.
- Cold field-emitter can achieve 0.3 eV; more common Schottky emitter 0.7 eV.
- Monochromator uses a slit in an energy dispersion plane to reduce ΔE .
- 0.15 eV achievable on Schottky system, 0.06 eV on a cold FEG.



P.C. Tiemeijer, *Inst. Phys. Conf. Ser.* **161**, 191 (1999).

P.E. Batson, H. W. Mook, P. Kruit, *Inst. Phys. Conf. Ser.* **165**, 213 (2000)

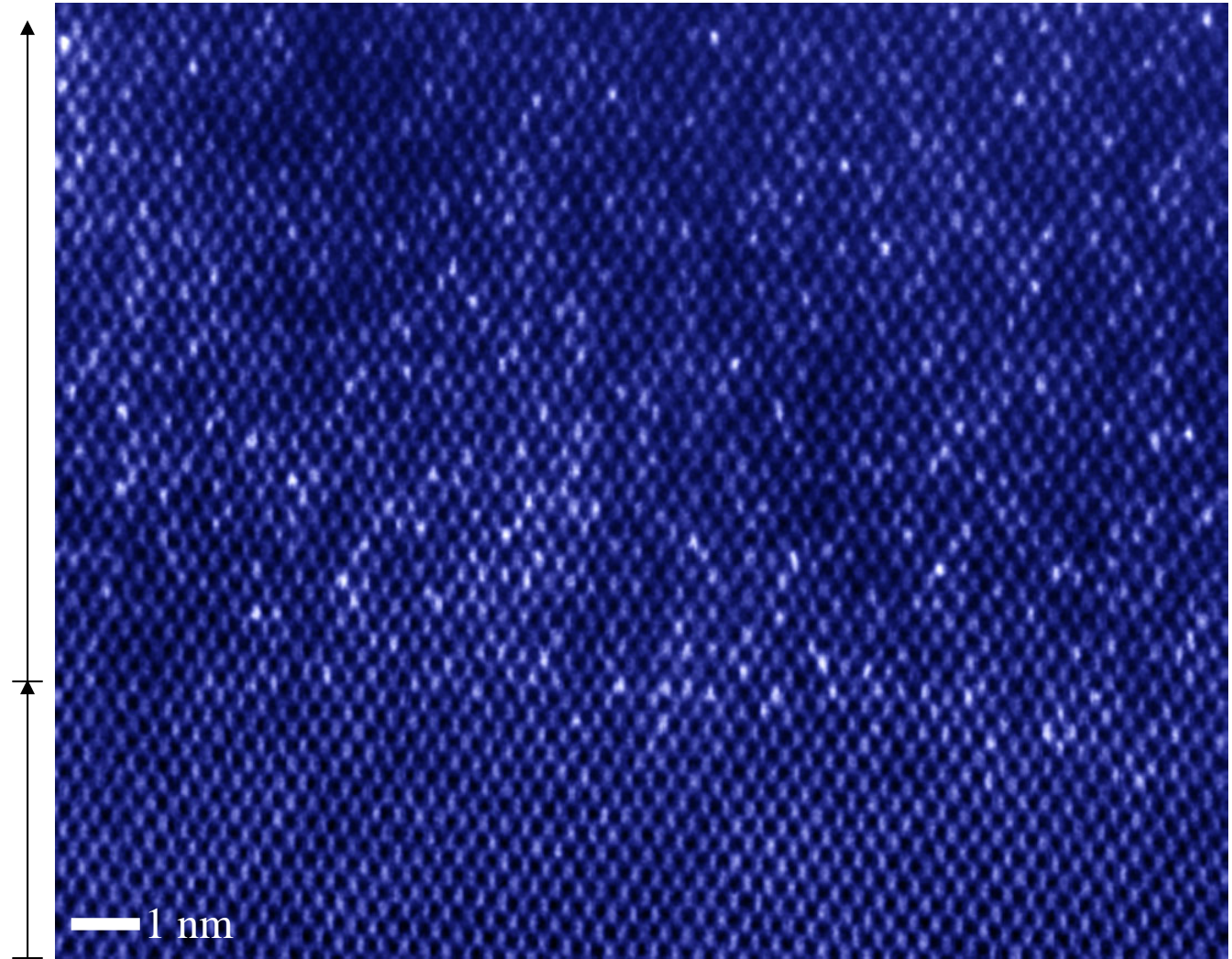
DoE TEAM Project

- TEAM = Transmission Electron Achromatic Microscope
- Build the world's first chromatic aberration corrected TEM.
- First instrument for NCEM @ LBL concentrated on highest achievable resolution.
- Subsequent instruments planned for other DoE e-beam centers @ UIUC, ORNL, and ANL.
- C_s and C_c correction could allow 1 Å resolution with a sample area of ~1 cm, allowing much more flexibility in *in situ* experiments.

Imaging Single Atoms

Sb source on

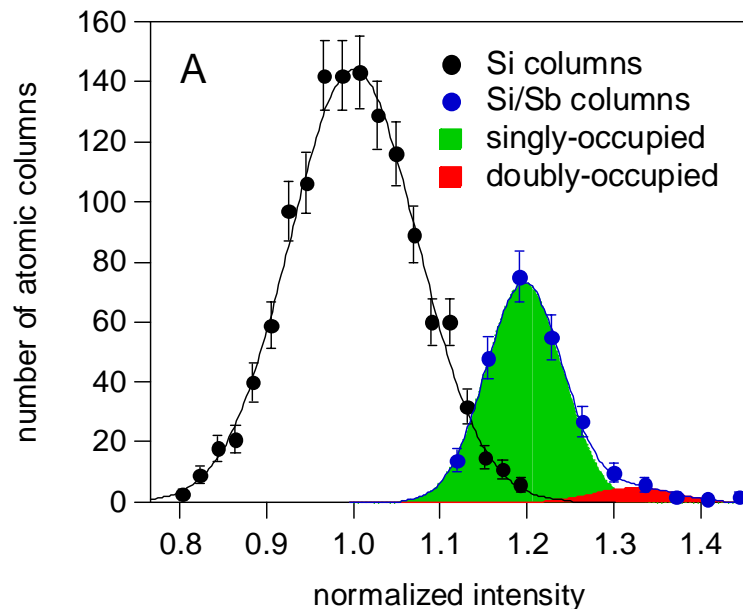
substrate



Most of the brightest dots are atomic columns with one Sb.

Imaging Single Atoms

	Image A		Image B	
# of Sb atoms	measured	predicted	measured	predicted
0	1300 (50)	1300	2240 (70)	2234
1	230 (30)	223	470 (40)	468
2	15 (15)	17	20 (20)	45

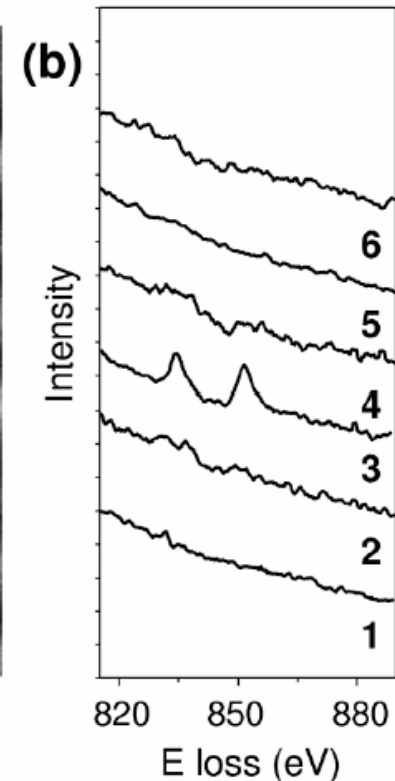
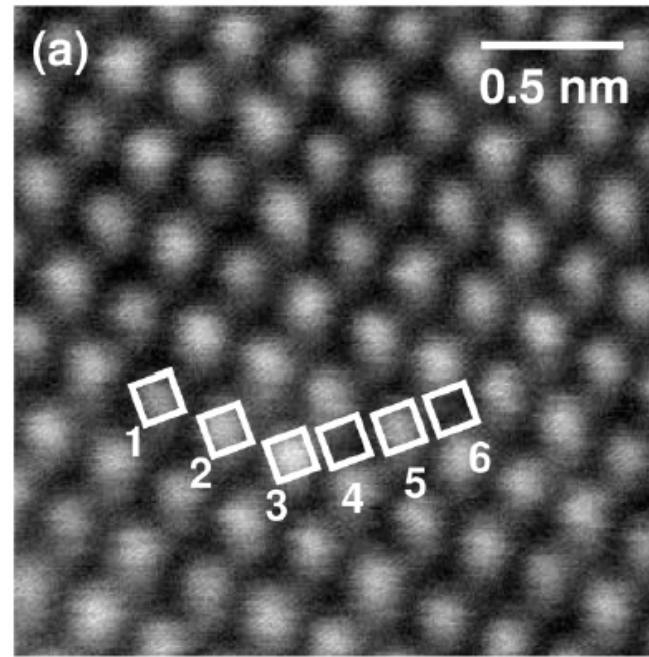


Results are consistent with random substitution of Sb on Si sites, measured with single-Sb sensitivity and ~100 % Sb detection efficiency.

First time single atoms have been imaged *in the bulk!*

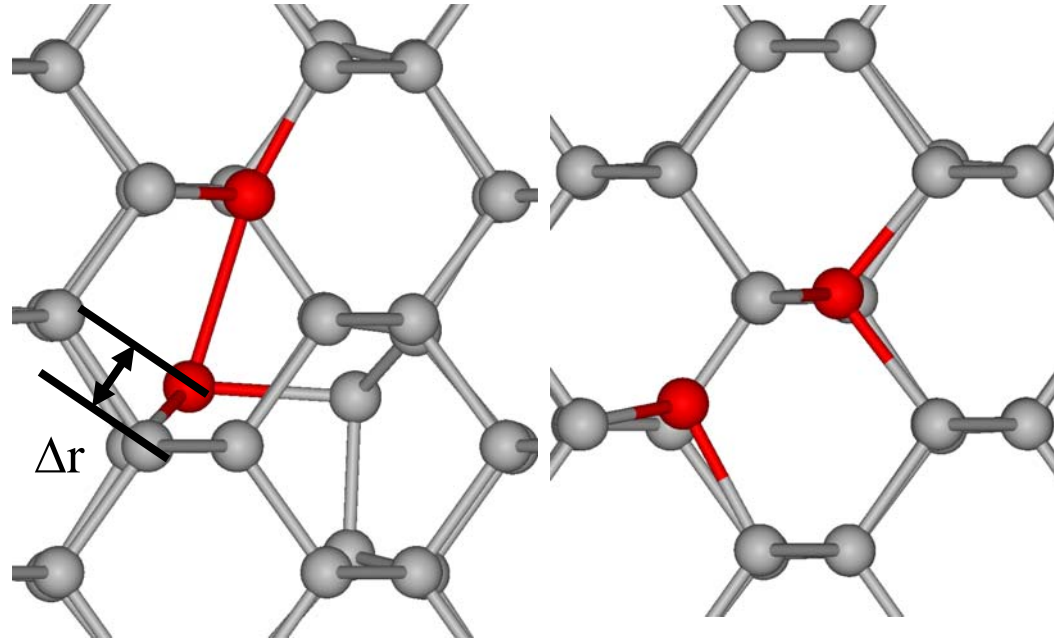
Chemistry of Single Atoms

- Varela et al. Phys. Rev. Lett. **92**, 095502
- Aberration corrected STEM.
- Sample is lightly La doped CaTiO_3
- Column 3 contains one La atom; spectrum 3 shows La $M_{4,5}$ edge
- Column 2 is Ti, shows ~10 % intensity in EELS
- Column 4 is O, shows ~20 % intensity in EELS
- Points the way to single-atom electronic structure
 - valence of isolated impurities
 - natural or artificial charge ordering
 - trap states in semiconductors



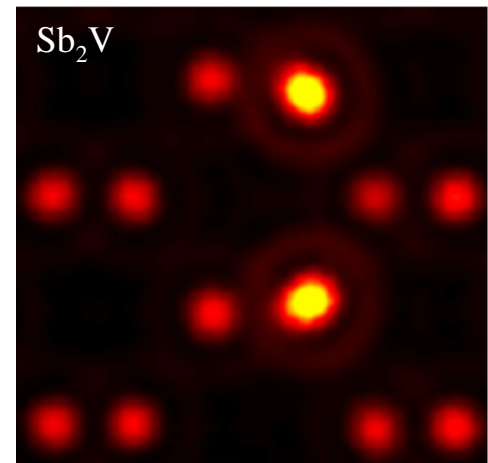
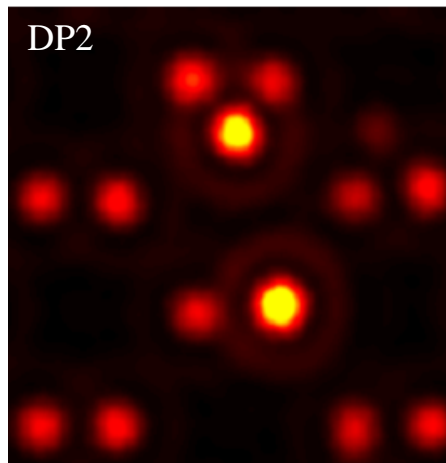
Point Defect Complexes in Si

- At high concentration, donor impurities stop donating in Si.
- Various donor / point defect clusters proposed.
- Can't see the point defects directly, but with a aberration corrected STEM could see the off-site displacement of the heavy donor atoms.



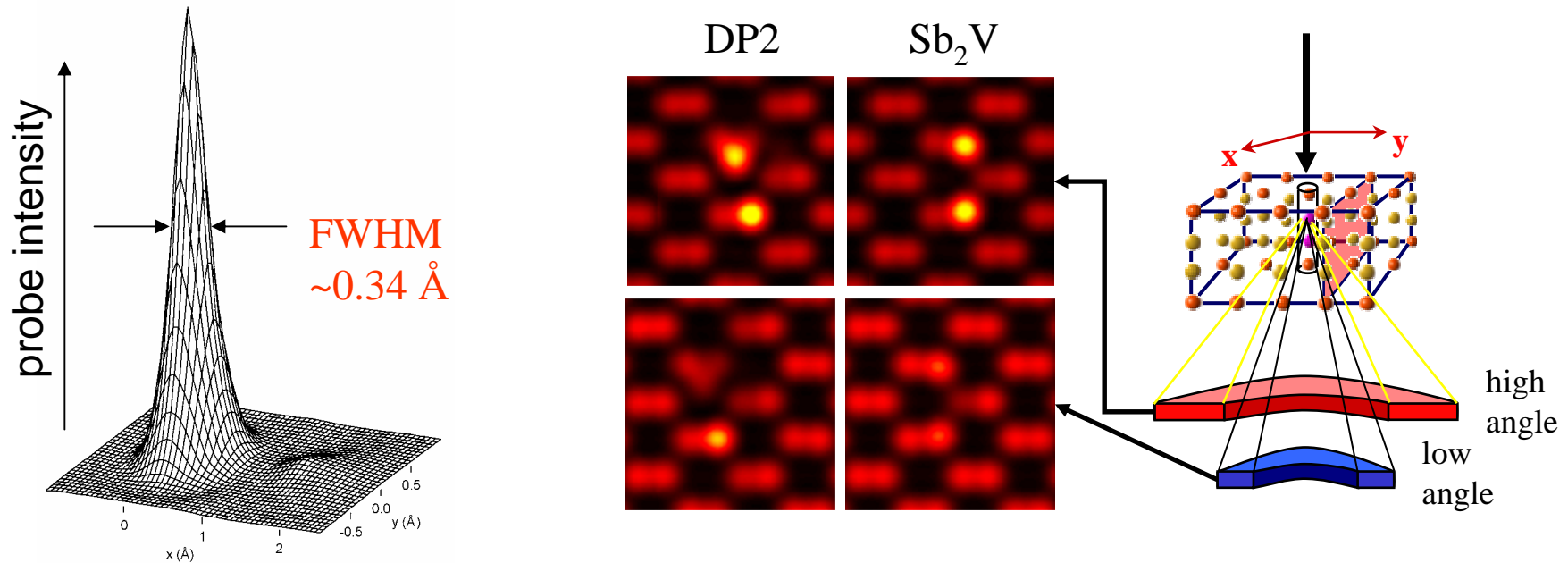
DP2

Sb₂V



Simulated aberration-
corrected STEM images

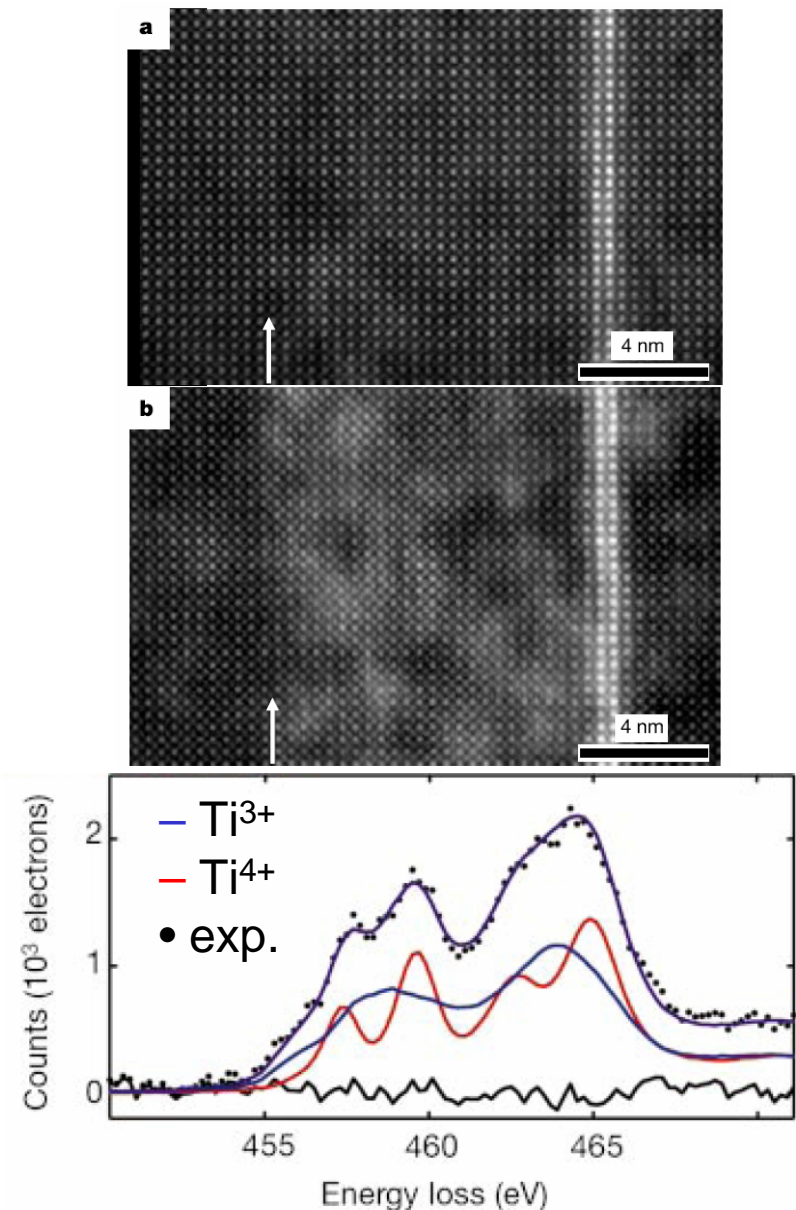
Probe Channeling



- Probe e^- couple to $1s$ state localized on the atomic column, acting like a local resolution boost for on-site impurities.
- Compare high-angle image emphasizing heavy atoms, to low-angle image emphasizing the lattice: Sb with large Δr will disappear.
- Result is that all Sb's have $\Delta r < 0.3 \text{ \AA}$, requiring a new model for the electrically deactivating defect.
- Voyles et al. PRL **91**, 125505 (2003).

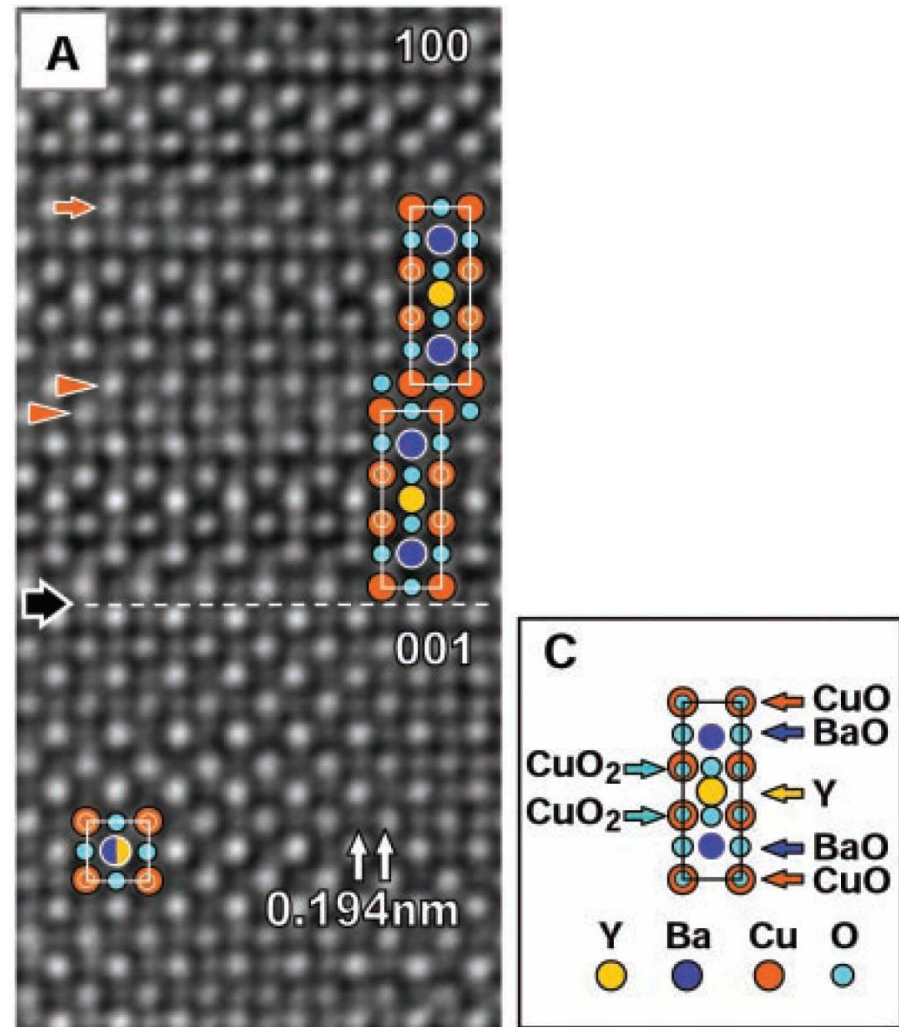
O Vacancies in SrTiO₃

- Muller et al., Nature **430**, 657 (2004).
- PLD homoepitaxial SrTiO_{3- δ} ; δ varied by O partial pressure
- Vacancies appear in
 - O K-edge fine structure directly
 - Ti L_{2,3} edge, which is sensitive to Ti valence
 - LAADF image via strain-induced dechanneling
- Detection limit 1-4 O_V



Imaging Anions Directly

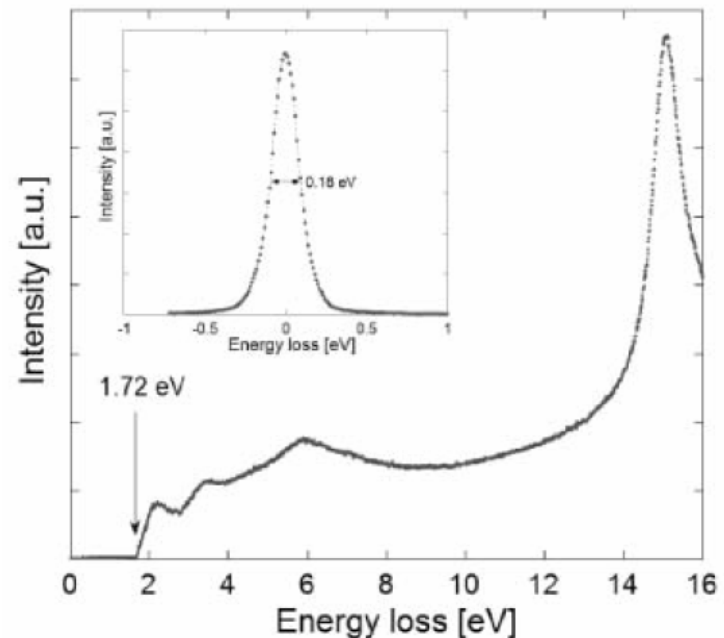
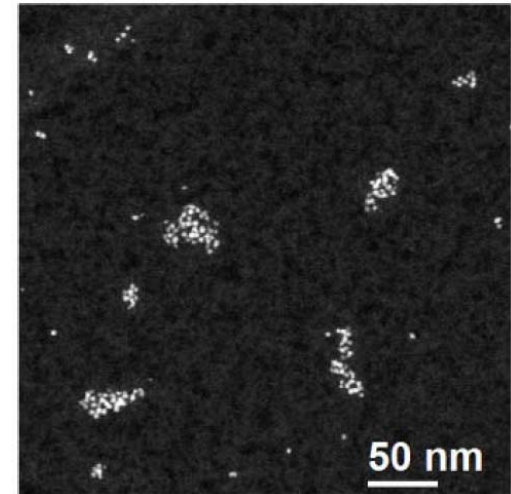
- Jia et al. Science **299**, 871 (2003).
- C_s corrected TEM gives phase contrast, which is more sensitive to light atoms.
- O columns between Cu/O columns are resolved.
- Recent reports of detecting O vacancies by quantifying contrast, but have not been demonstrated on well-controlled samples.



90° tilt boundary in $\text{YBa}_2\text{Cu}_3\text{O}_7$

Interband Scattering by EELS

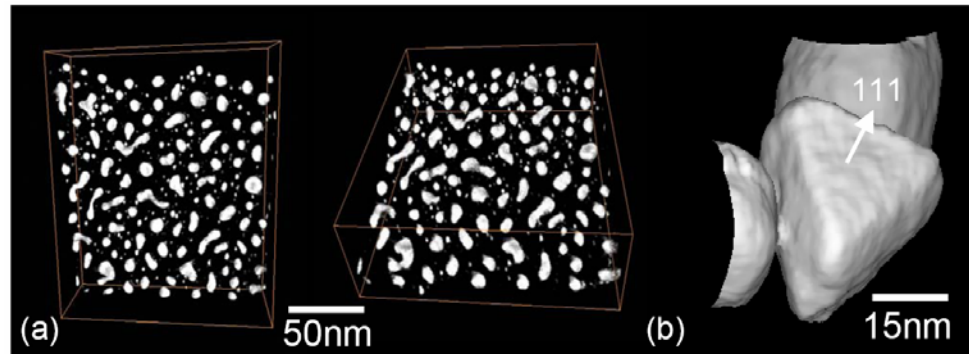
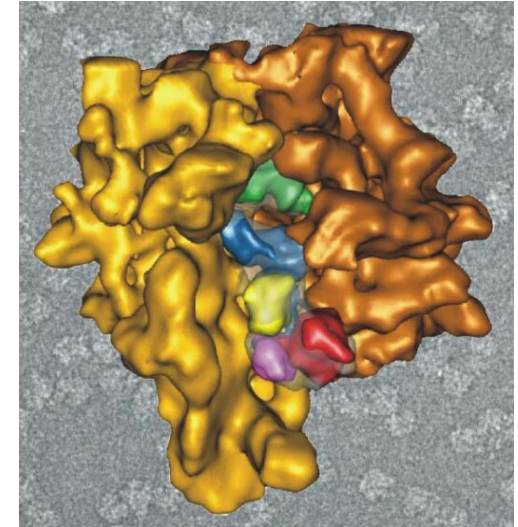
- High ΔE from monochromator makes transition to conduction band visible in low-loss EELS.
- Measurements on single nanostructures:
 - Correlate bandgap, surface states, etc. with size, shape, atomic structure, and surface chemistry.
 - Measure anisotropy in single quantum dots.
 - R. Ermi, N. D. Browning, *Microsc. Microanal.* **10 Suppl. 2**, 842 (2004).
- Band bending at e.g. interfaces, edges of quantum wells.



3D: Tomography

- Requires monotonic intensity response with thickness.
- Commonplace in biology, where diffraction effects are minimal.
- Z-contrast STEM & energy-filtered TEM are enabling materials applications.
- 1 nm resolution achievable in 3D.
- EFTEM adds chemical information.

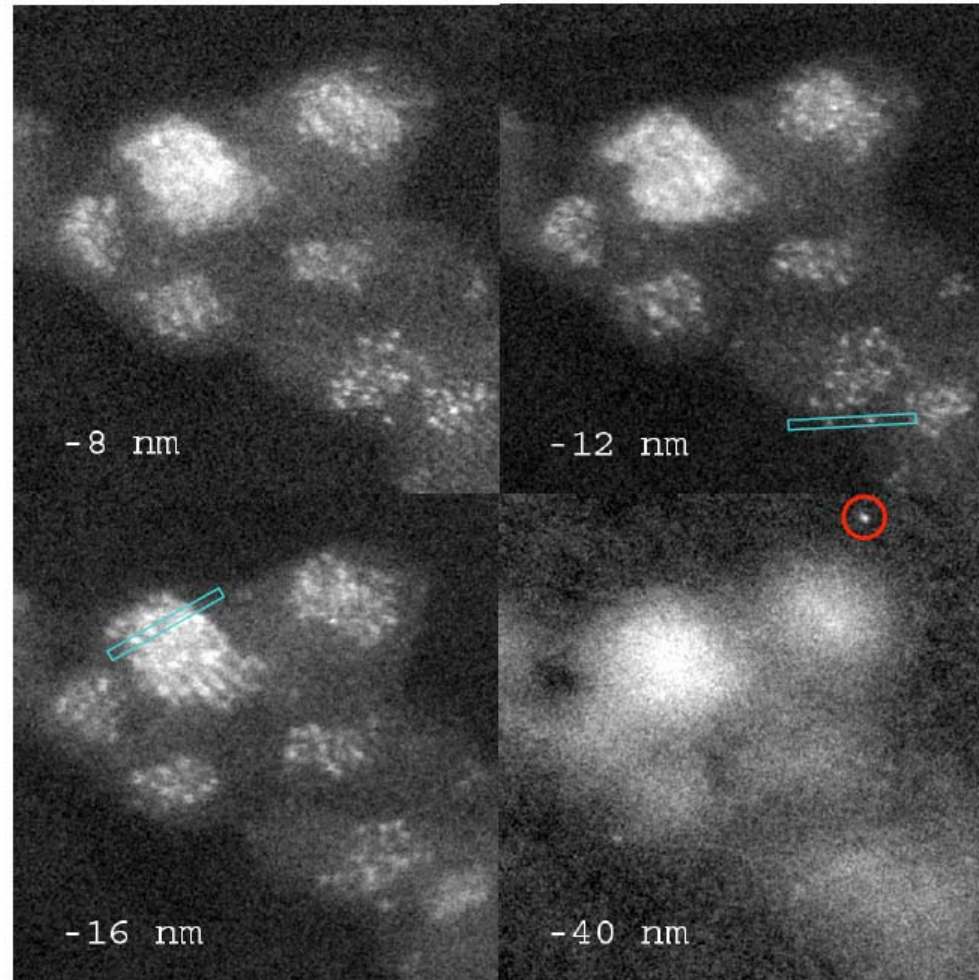
J. Harms et al.,
Structure Fold Des
7, 931-41. (1999)



P. A. Midgley et al., Microsc. Microanal. **10 Suppl. 3**, 148 (2004).

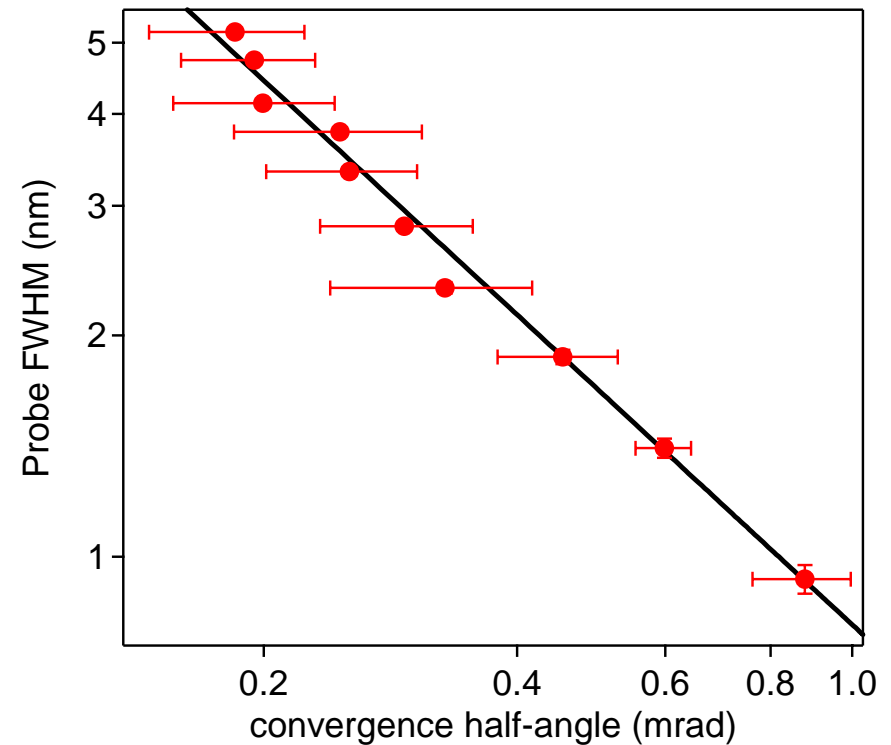
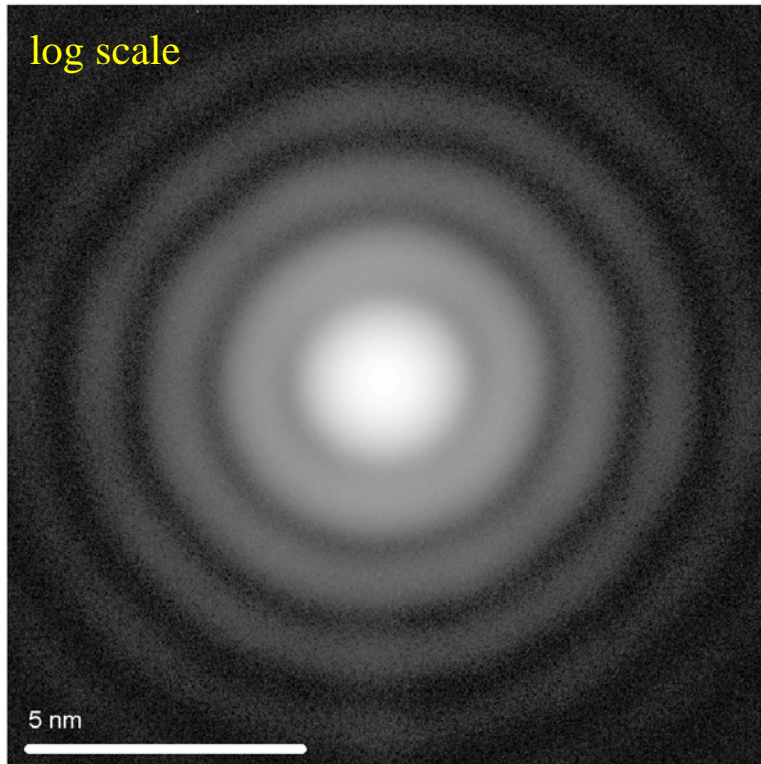
3D: Optical Sectioning

- Aberration correction means larger numerical apertures, limited depth of field.
- 3D imaging by a defocus series; optical sectioning.
- Current instruments vertical resolution of 6 nm
- Next generation 1.5 nm.



Through focus series of Pt_2Ru_4 catalyst on a-C support. Pennycook et al. Microsc. Microanal. **10 Suppl. 3**, 1172 (2004).

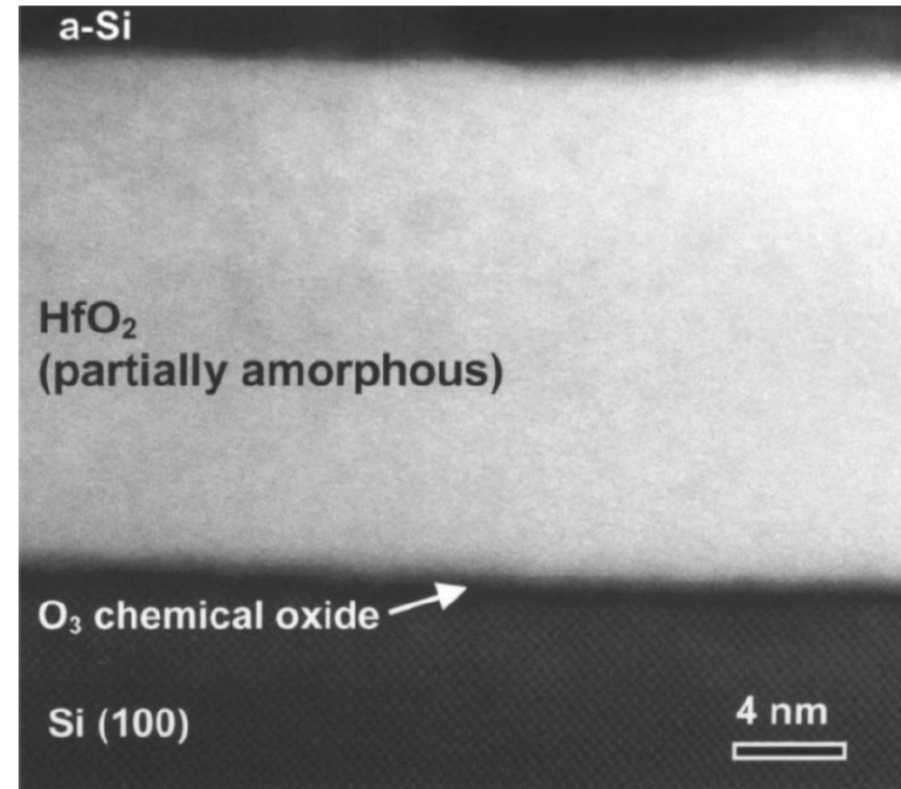
Coherent Scattering



- High brightness field-emission sources can create coherent electron probes 0.5 – 5 nm in diameter.

Amorphous Thin Films

- Pair distribution function is the basic structural diagnostic for amorphous materials.
- McBride [Ultramic. **76**, 115 (1999)] developed a method for measuring PDF from ~ 2 nm volumes by deconvolution of convergent probe.
- Useful for thin films, interface layers, integrannular layers.



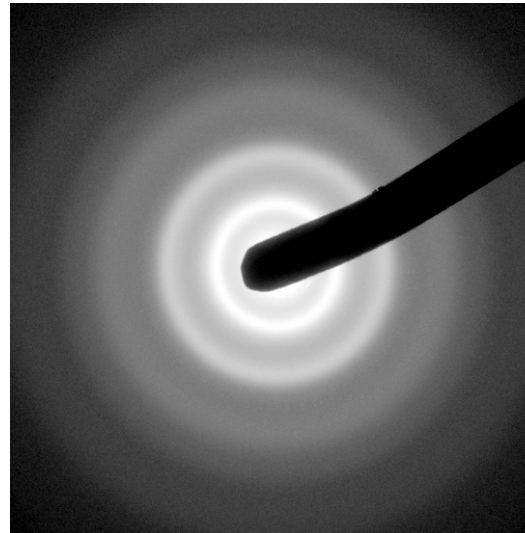
HfO₂ replacement gate dielectric with “amorphous” but heavily ordered structure (Ho et al. JAP **93**, 1477 (2003)).

Spatial Fluctuations in Diffraction

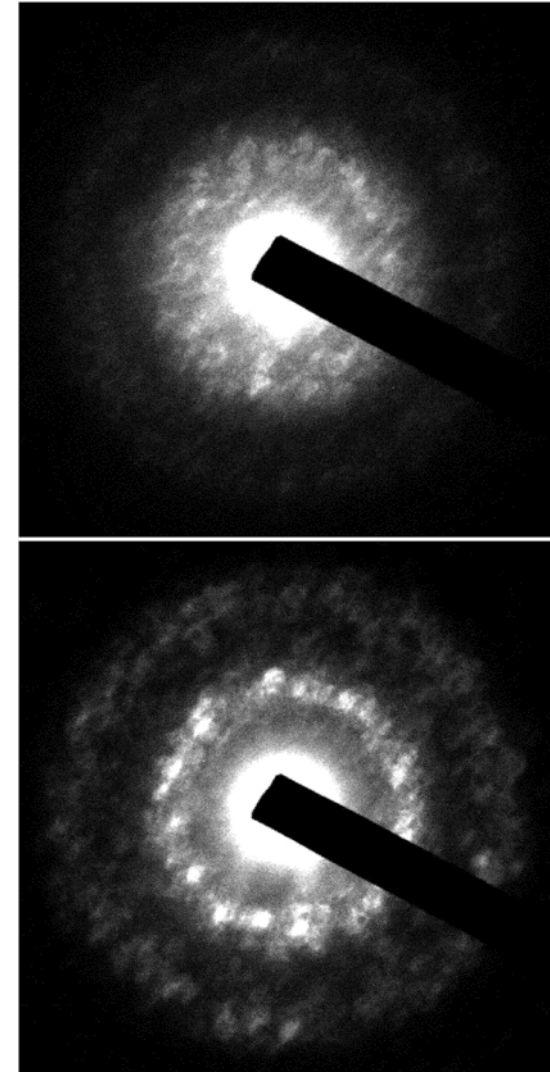
- Coherent probe size \cong structural correlation length.
- Magnitude of spatial fluctuations reveals heterogeneities in amorphous structure.
- Spatial analogy to photon correlation spectroscopy.

Different 1.5 nm areas:

Large area:
average $S(q)$



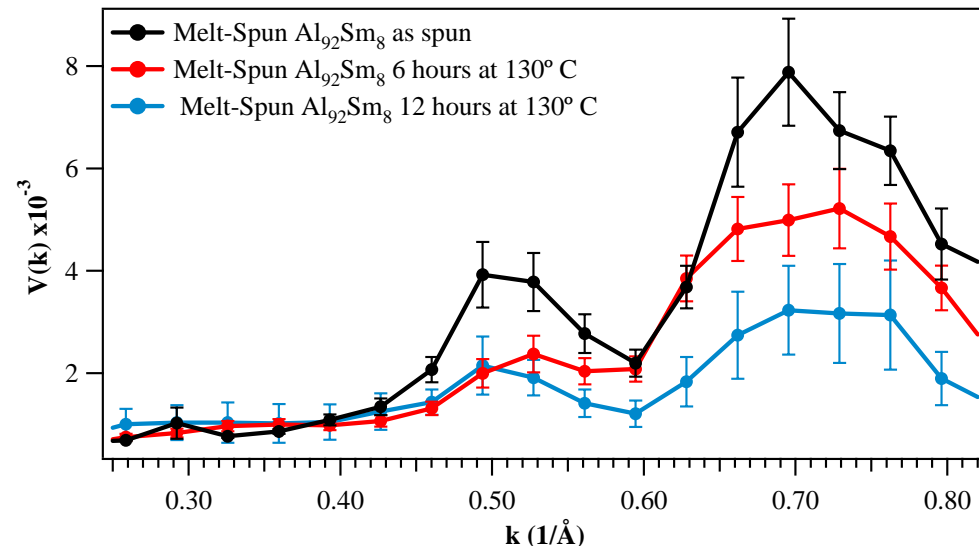
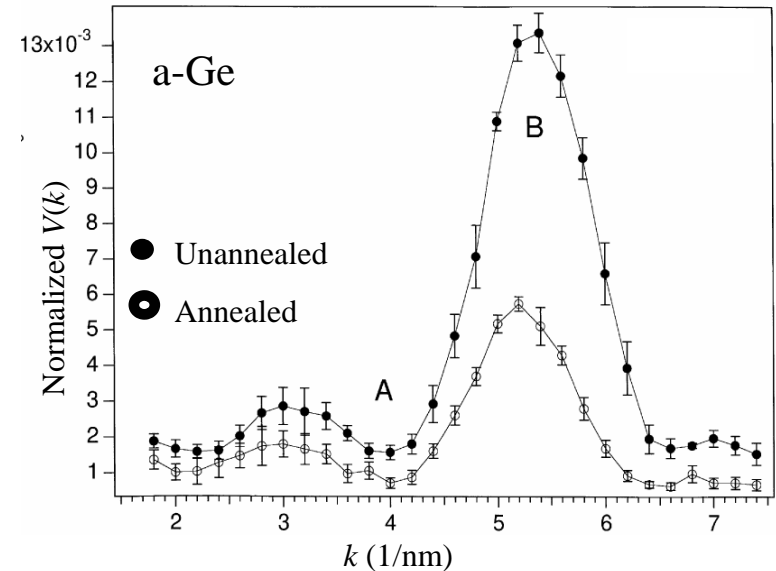
Voyles and Muller,
Ultramicroscopy **93**,
147 (2002).



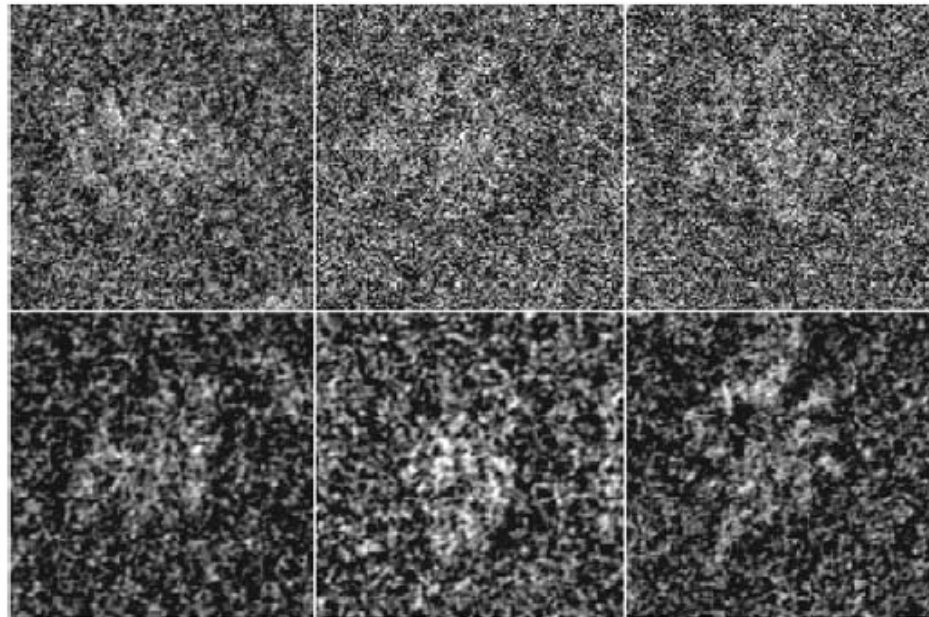
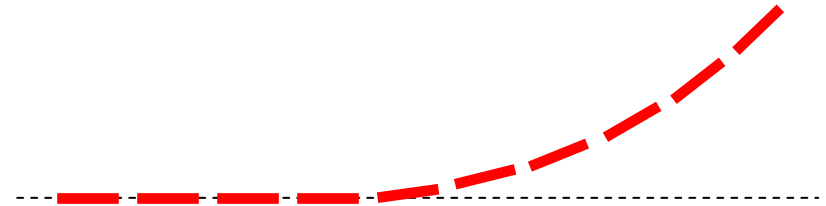
0.3 \AA^{-1}

Fluctuation TEM

- Real amorphous semiconductors are not ideal continuous random networks (Gibson and Treacy PRL **78**, 1074 (1997)).
- Al-Sm metallic glass with high critical cooling rate contains structural order (Stratton et al. MRS Proc. **806** M9.4 (2003)).



- Persistence length in polymers from angular correlation along the chain.
- Phase separation in block copolymers
- Proteins
 - single particles in amorphous ice
 - set of many single-particle patterns contain more data than the average



70S ribosomes from *e. coli* imaged in different orientations (Gao et al. Ultramicroscopy **93**, 169 (2002))

Perennial Limitations

- Samples must be thin
 - <10 nm for high-resolution measurements on typical crystals
- Samples must be in vacuum
 - Some environmental cell work in gas (Lee et al. Rev. Sci. Inst. **62**, 1438 (1991)) and now liquid environments (Williamson et al. Nature Materials **2**, 532 (2003)).
- **Radiation damage**
 - Several applications (e.g. spectroscopic identification of oxygen vacancies) limited by signal to noise, which is fundamentally limited by damage.
 - 3D imaging will require very high dose.

- Current or near-future EM offers:
 - Structural and chemical characterization at sub-Ångstrom resolution and single atom sensitivity.
 - Characterization of point defects under the right conditions.
 - <0.2 eV resolution spectroscopy of individual nanostructures, impurities, & defects.
 - 3D, nanometer resolution imaging
 - Nanoscale coherent scattering for characterization of amorphous materials